

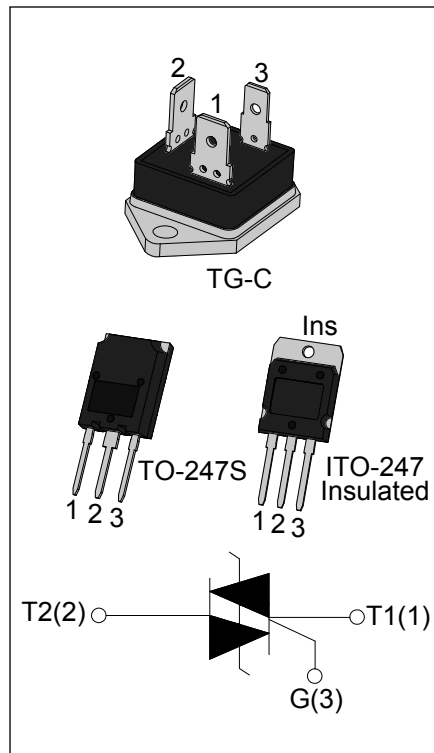


### DESCRIPTION:

With high ability to withstand the shock loading of large current, JST80 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load. From all three pins to external heatsink, JST80IS triac provides an insulation voltage of 2500 V<sub>RMS</sub>, complying with UL standards. (File: E252906) All the packages are RoHS compliant. (2011/65/EU)

### MAIN FEATURES

Symbol	Value	Unit
I <sub>T(RMS)</sub>	80	A
V <sub>DRM</sub> / V <sub>RRM</sub>	1200/1600	V



### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Storage junction temperature range	T <sub>stg</sub>	-40-150	°C	
Operating junction temperature range	T <sub>j</sub>	-40-125	°C	
Repetitive peak off-state voltage (T <sub>j</sub> =25°C)	V <sub>DRM</sub>	1200/1600	V	
Repetitive peak reverse voltage (T <sub>j</sub> =25°C)	V <sub>RRM</sub>	1200/1600	V	
RMS on-state current	I <sub>T(RMS)</sub>	TO-247S/ ITO-247(Ins) (T <sub>C</sub> =85°C)	80	A
		TG-C (T <sub>C</sub> =90°C)		
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I <sub>TSM</sub>	800	A	
I <sup>2</sup> t value for fusing (tp=10ms)	I <sup>2</sup> t	3200	A <sup>2</sup> s	
Critical rate of rise of on-state current (I <sub>G</sub> = 2 × I <sub>GT</sub> )	dI/dt	100	A/μs	

Peak gate current	$I_{GM}$	8	A
Average gate power dissipation	$P_{G(AV)}$	2	W
Peak gate power	$P_{GM}$	10	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}C$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
$I_{GT}$	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	mA
$V_{GT}$		I - II -III	MAX	1.3	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^{\circ}C$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	80	mA
		II		120	
$I_H$	$I_T=100mA$		MAX	70	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}C$		MIN	1500	V/ $\mu$ s

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=120A t_p=380\mu s$	$T_j=25^{\circ}C$	1.5	V
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	20	$\mu$ A
$I_{RRM}$		$T_j=125^{\circ}C$	10	mA
$V_{TO}$	Threshold voltage	$T_j=125^{\circ}C$	0.95	V
$R_d$	Dynamic resistance	$T_j=125^{\circ}C$	8.5	m $\Omega$

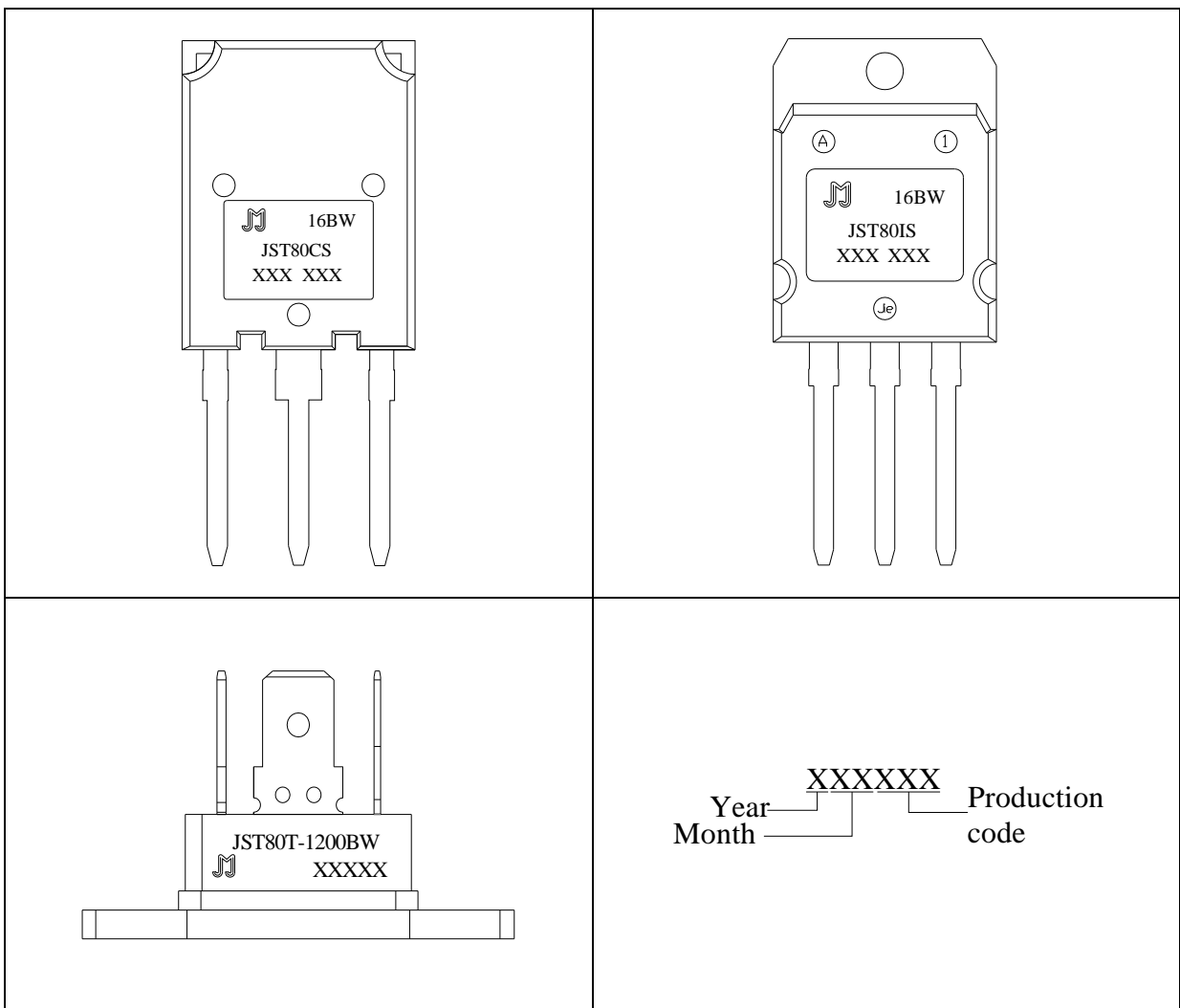
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-247S	0.35	$^{\circ}C/W$
		ITO-247 (Ins)		
		TG-C	0.31	

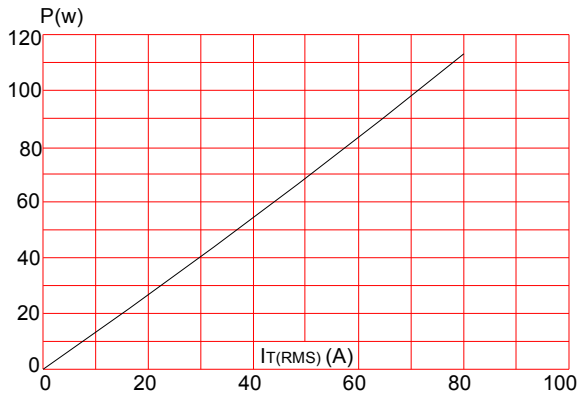
ORDERING INFORMATION

<p><b>J</b></p> <p>JieJie Microelectronics Co.,Ltd</p>	<p><b>ST</b></p> <p>Triacs</p> <p><math>I_{T(RMS)}:80A</math></p> <p>T:TG-C CS:TO-247S IS:ITO-247(Ins)</p>	<p><b>80</b></p>	<p><b>CS</b></p>	<p><b>-1200</b></p> <p>1200:VDRM/VRRM<math>\geq</math>1200V 1600:VDRM/VRRM<math>\geq</math>1600V</p>	<p><b>BW</b></p> <p>BW:IGT1-3<math>\leq</math>50mA</p>	<p><b>-/</b></p> <p>Blank: Tube</p>
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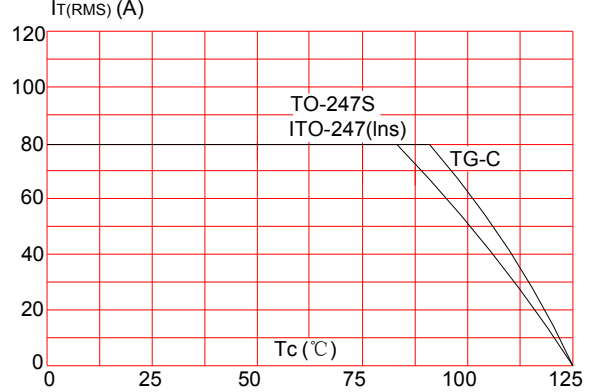
MARKING



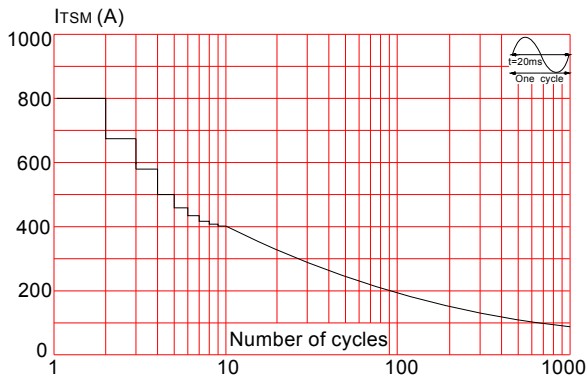
**FIG.1:** Maximum power dissipation versus RMS on-state current



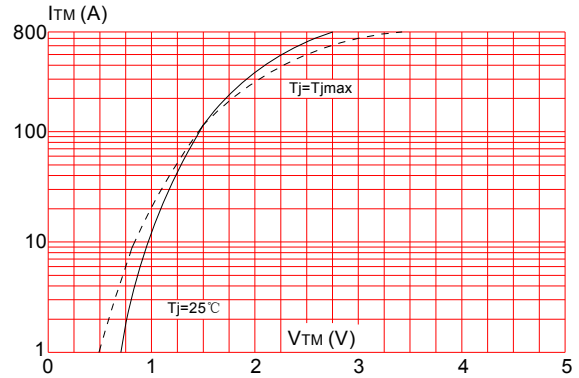
**FIG.2:** RMS on-state current versus case temperature



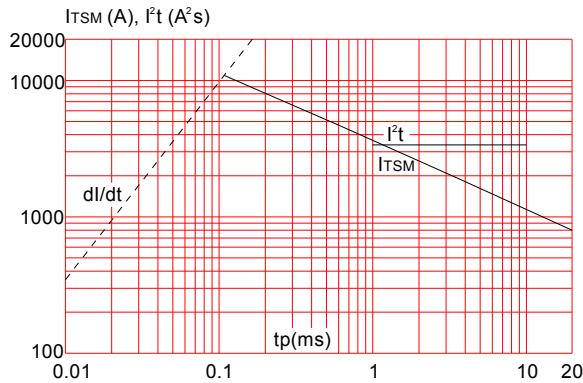
**FIG.3:** Surge peak on-state current versus number of cycles



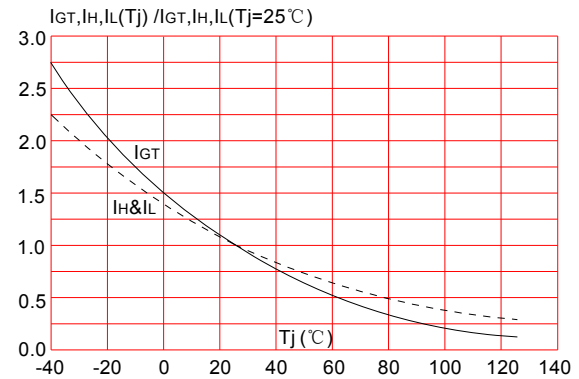
**FIG.4:** On-state characteristics (maximum values)



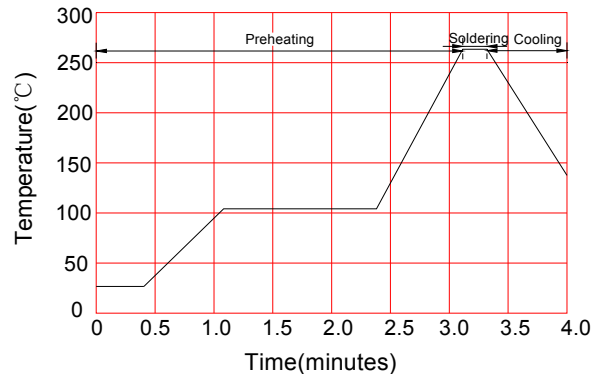
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



**Wave Soldering**



Item	Conditions
Peak Temperature	265°C
Dipping Time	10 seconds
Soldering	1 time

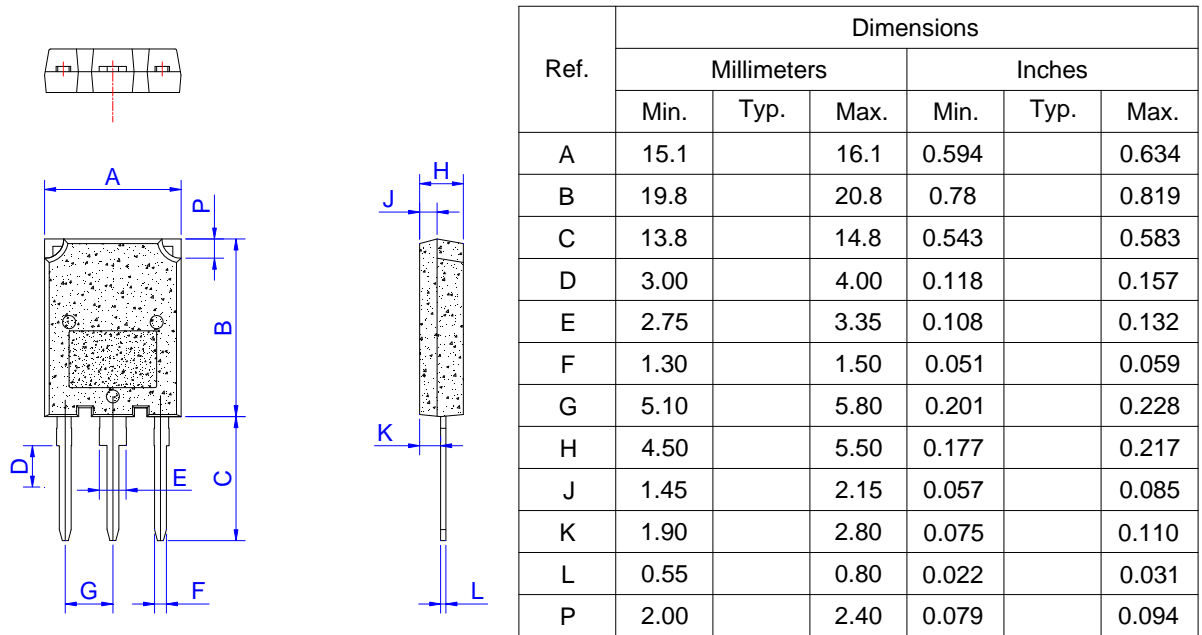
**ORDERING INFORMATION**

Order code	Voltage V <sub>DRM</sub> /V <sub>RPM</sub> (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST80T-1200/1600BW	1200/1600	50	TG-C	10	Tube
JST80CS-1200/1600BW			TO-247S	30	
JST80IS-1200/1600BW			ITO-247	25	

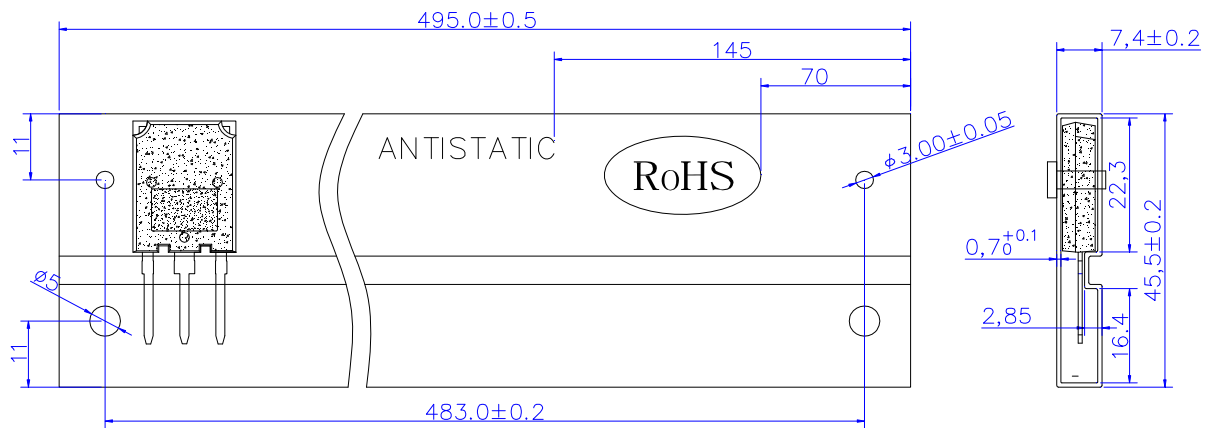
**Document Revision History**

Date	Revision	Changes
July 22, 2021	8	Add Vto & Rd

PACKAGE MECHANICAL DATA

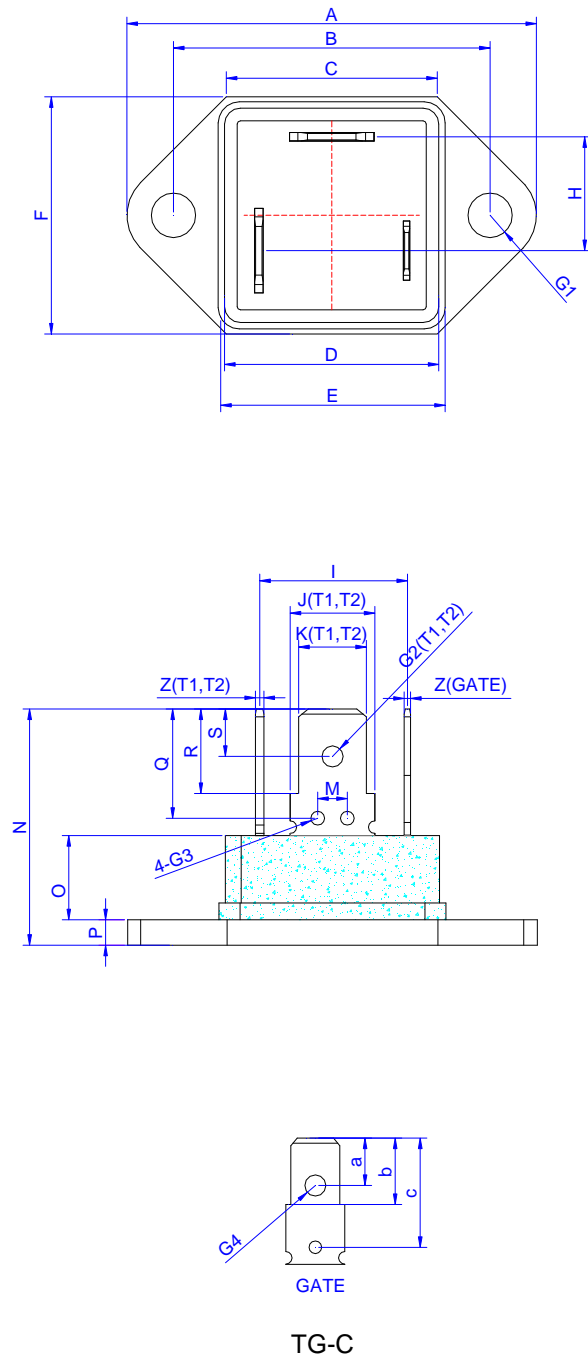


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-247S	TUBE	30	450	2,250

**PACKAGE MECHANICAL DATA**



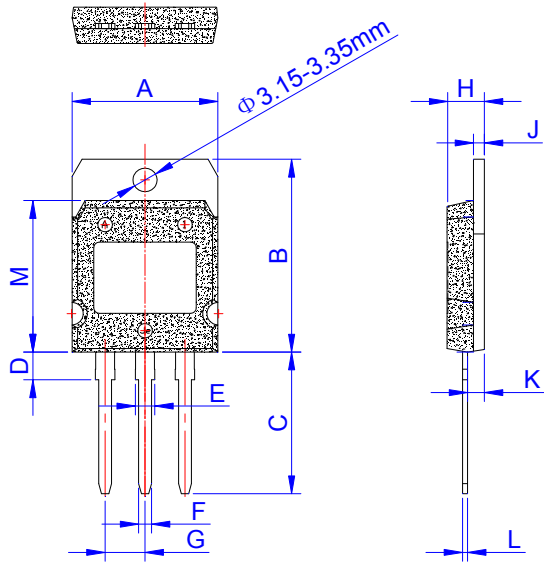
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			39.2			1.543
B	29.8	30.0	30.2	1.173	1.181	1.189
C			20.2			0.795
D			20.5			0.807
E			21.6			0.85
F			23			0.905
G1	Φ4.1	Φ4.2	Φ4.3	Φ0.161	Φ0.165	Φ0.169
H		10.3			0.406	
I		13.9			0.547	
J(T1,T2)		8			0.315	
K(T1,T2)		6.4			0.252	
M	2.7	3.0	3.3	0.106	0.118	0.130
N			22.8			0.898
O		8.2			0.323	
P		2.5			0.098	
Q	9.45	9.75	10.1	0.374	0.383	0.398
R	7.8	7.95	8.1	0.307	0.313	0.319
S	4.3	4.5	4.7	0.169	0.177	0.185
Z(T1,T2)	0.78	0.8	0.85	0.0307	0.0315	0.0335
G2(T1,T2)		Φ2	Φ2.2		Φ0.079	Φ0.087
G3	Φ1.1	Φ1.3	Φ1.5	Φ0.043	Φ0.051	Φ0.059
G4		Φ1.55	Φ1.75		Φ0.061	Φ0.069
a	2.95	3.15	3.35	0.116	0.124	0.132
b	6.2	6.35	6.5	0.244	0.25	0.256
c	9.35	9.75	10	0.368	0.384	0.393
Z(GATE)	0.58	0.6	0.65	0.0228	0.0236	0.0256
J(GATE)		5.6			0.221	
K(GATE)		4.65			0.183	

**DELIVERY MODE**

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TG-C	TUBE	10	100	500

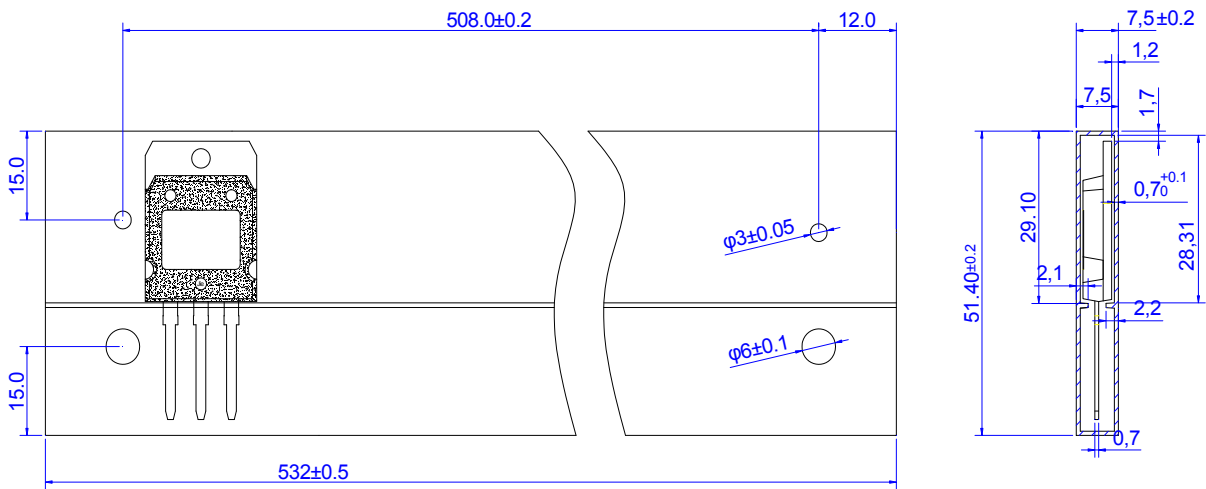


PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	19.7	19.9	20.1	0.776	0.783	0.791
B	26.9	27.1	27.3	1.059	1.067	1.075
C	19.4	19.9	20.4	0.764	0.783	0.803
D	3.80	3.90	4.00	0.150	0.154	0.157
E	2.56	2.66	2.76	0.101	0.105	0.109
F	1.66	1.76	1.86	0.065	0.069	0.073
G		5.45			0.215	
H	5.05	5.10	5.50	0.199	0.201	0.217
J	1.45	1.50	1.55	0.057	0.059	0.061
K	2.20	2.30	2.40	0.087	0.091	0.094
L	0.60	0.70	0.80	0.024	0.028	0.031
M	21.2	21.3	21.4	0.835	0.839	0.843

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
ITO-247	TUBE	25	400	1,600



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